TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process)

2SB907

Switching Applications

Hammer Drive, Pulse Motor Drive Applications

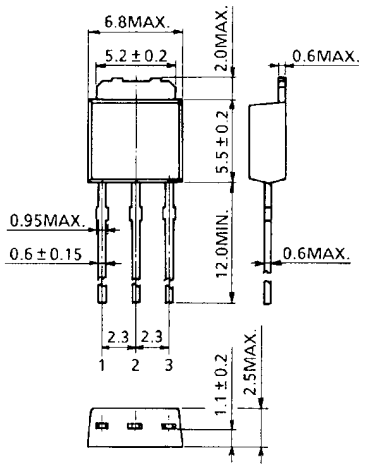
Power Amplifier Applications

- High DC current gain: $h_{FE\ (1)}$ = 2000 (min) (V_{CE} = −2 V, I_C = −1 A)
- Low saturation voltage: $V_{CE\ (sat)}$ = −1.5 V (max) (I_C = −2 A)
- Complementary to 2SD1222.

Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Collector-base voltage		V_{CBO}	−60	V
Collector-emitter voltage		V_{CEO}	−40	V
Emitter-base voltage		V_{EBO}	−5	V
Collector current		I_C	−3	A
Base current		I_B	−0.3	A
Collector power dissipation	Ta = 25°C	P_C	1.0	W
	Tc = 25°C		15	
Junction temperature		T_j	150	°C
Storage temperature range		T_{stg}	−55 to 150	°C

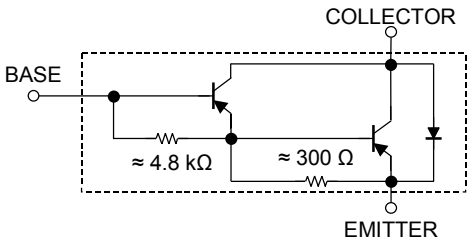
Unit: mm

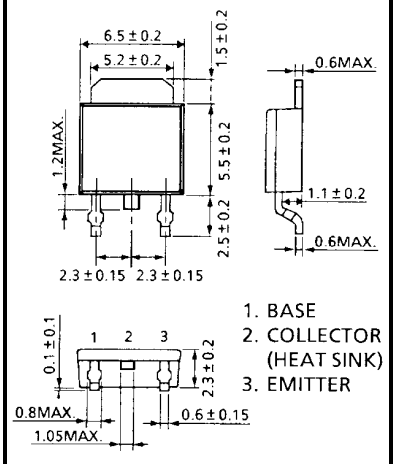


JEDEC	—
JEITA	—
TOSHIBA	2-7B1A

Weight: 0.36 g (typ.)

Equivalent Circuit

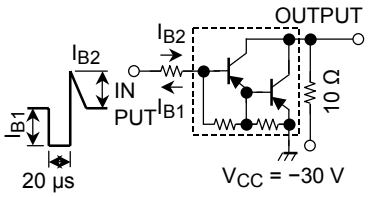




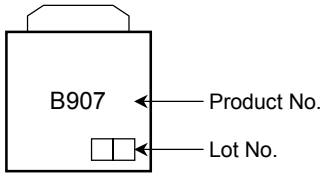
JEDEC	—
JEITA	—
TOSHIBA	2-7J1A

Weight: 0.36 g (typ.)

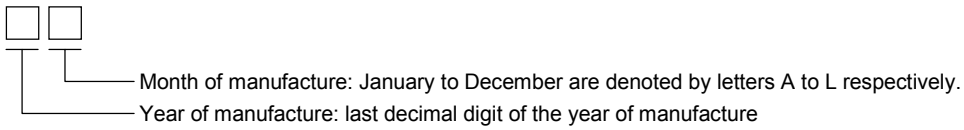
Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current		I_{CBO}	V_{CB} = −60 V, I_E = 0	—	—	−20	μA
Emitter cut-off current		I_{EBO}	V_{EB} = −5 V, I_C = 0	—	—	−2.5	mA
Collector-emitter breakdown voltage		$V_{(BR)\ CEO}$	I_C = −25 mA, I_B = 0	−40	—	—	V
DC current gain		$h_{FE\ (1)}$	V_{CE} = −2 V, I_C = −1 A	2000	—	—	
		$h_{FE\ (2)}$	V_{CE} = −2 V, I_C = −3 A	1000	—	—	
Collector-emitter saturation voltage		$V_{CE\ (sat)}$	I_C = −2 A, I_B = −4 mA	—	—	−1.5	V
Base-emitter saturation voltage		$V_{BE\ (sat)}$	I_C = −2 A, I_B = −4 mA	—	—	−2.0	V
Switching time	Turn-on time	t_{on}		—	0.30	—	μs
	Storage time	t_{stg}		—	0.60	—	
	Fall time	t_f		—	0.25	—	
			$-I_{B1} = I_{B2}$ = 6 mA, DUTY CYCLE ≤ 1%				

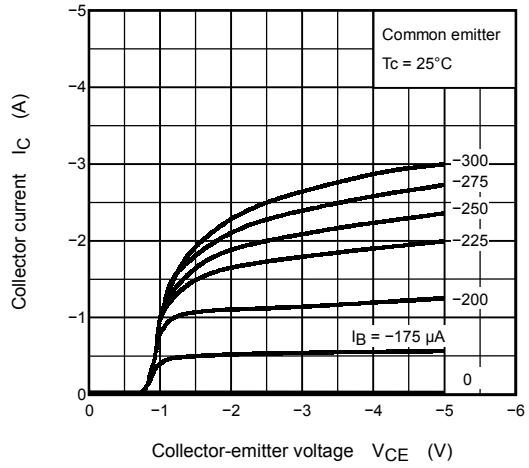
Marking



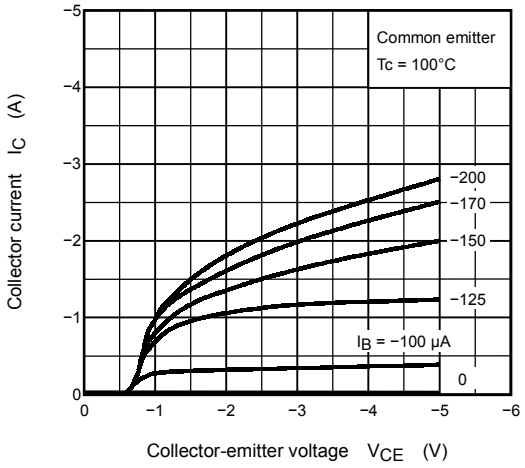
Explanation of Lot No.



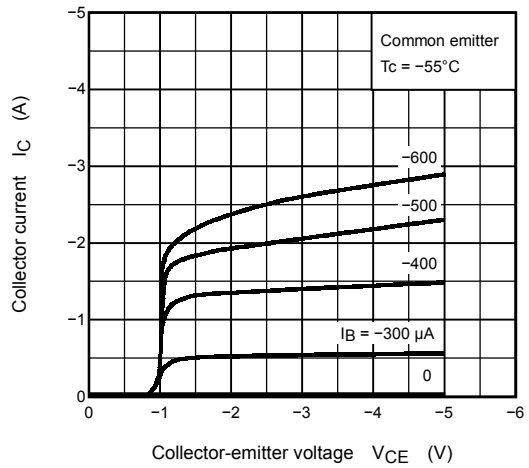
$I_C - V_{CE}$



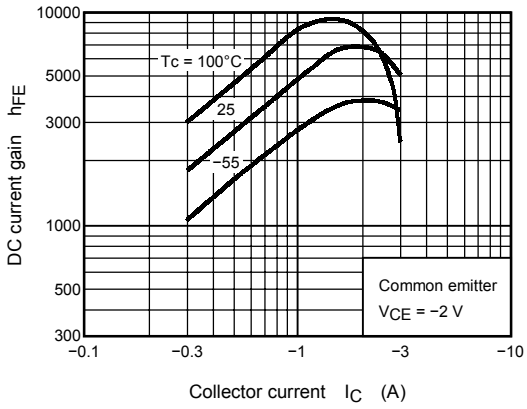
$I_C - V_{CE}$



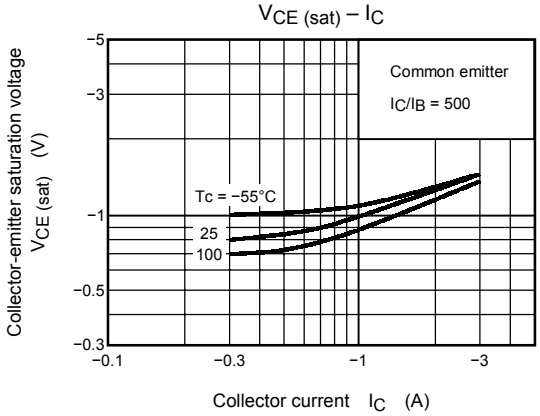
$I_C - V_{CE}$



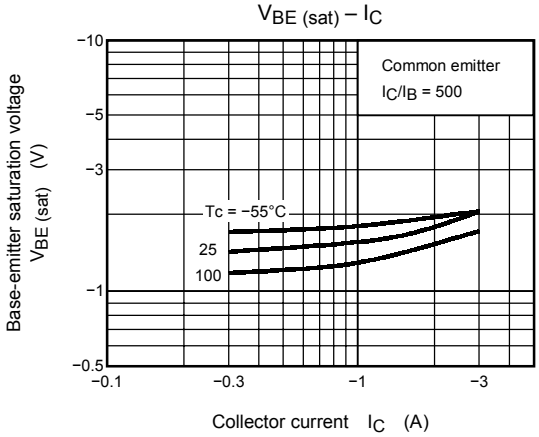
$h_{FE} - I_C$



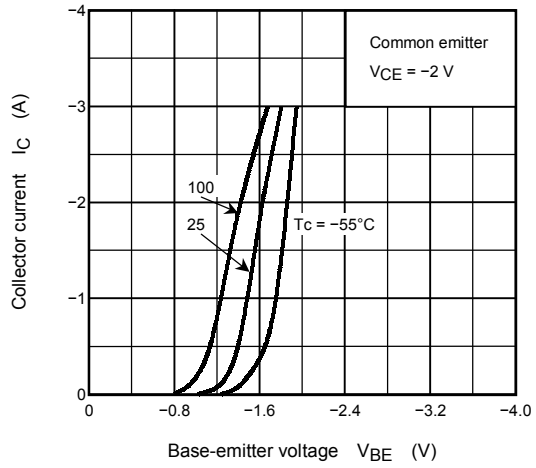
$V_{CE\ (sat)} - I_C$



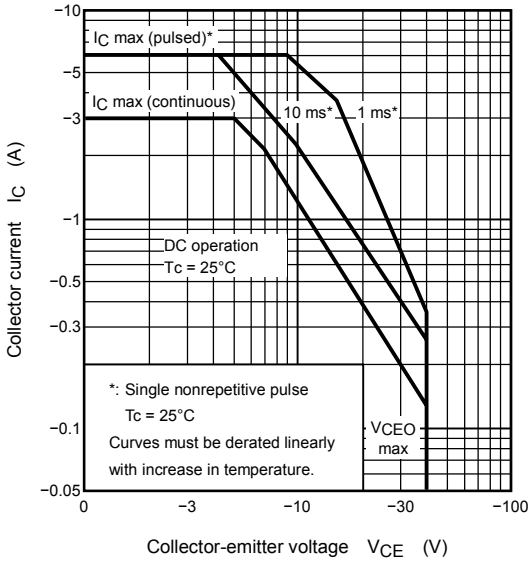
$V_{BE\ (sat)} - I_C$



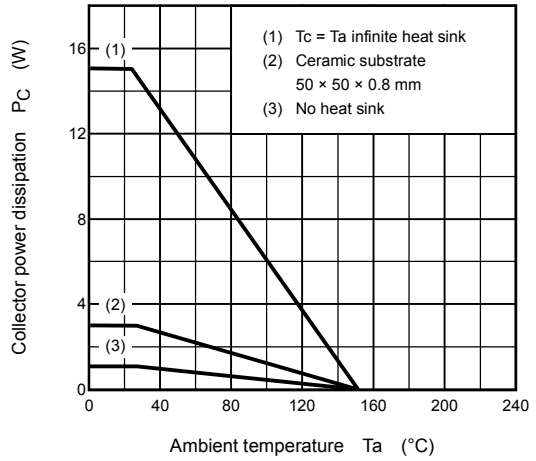
$I_C - V_{BE}$



Safe Operating Area



$P_C - Ta$



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